HITACHI

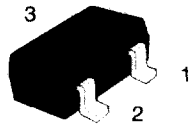
2SK1532

Silicon N Channel Junction FET
Low Frequency Amplifier, Analog Switching

Features

- Suitable for low frequency amplifier, variable resistance and analog switching circuit of audio equipment.
- Compact packages.

CMPAK



1. Drain
2. Source
3. Gate

Table 1 Absolute Maximum Ratings
(Ta = 25°C)

Item	Symbol	Rating	Unit
Gate to drain voltage	V_{GDO}	–50	V
Gate to source voltage	V_{GSS}	–50	V
Drain current	I_D	10	mA
Channel power dissipation	Pch	100	mW
Channel temperature	Tch	150	℃
Storage temperature	Tstg	–55 to +150	℃

Table 2 Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test condition
Gate to source breakdown voltage	$V_{(BR)GSS}$	–50	—	—	V	I_G = –100 µA, V_{DS} = 0
Gate cutoff current	I_{GSS}	—	—	–10	nA	V_{GS} = –30 V, V_{DS} = 0
Drain current	I_{DSS}*	0.6	—	6.5	mA	V_{DS} = 15 V, V_{GS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	–0.4	—	–5	V	V_{DS} = 15 V, I_D = 0.1 µA
Forward transfer admittance	$\|y_{fs}\|$	1.0	—	—	mS	V_{DS} = 15 V, V_{GS} = 0, f = 1 kHz
Input capacitance	Ciss	—	5.2	—	pF	V_{DS} = 15 V, V_{GS} = 0, f = 1 kHz
Output capacitance	Coss	—	1.5	—	pF	V_{DS} = 15 V, V_{GS} = 0, f = 1 kHz

* The 2SK1532 is grouped by I_{DSS} as follows.

Grade	B	C	D
Mark	XDB	XDC	XDD
I_{DSS}(mA)	0.6 to 1.4	1.2 to 3.0	2.6 to 6.5

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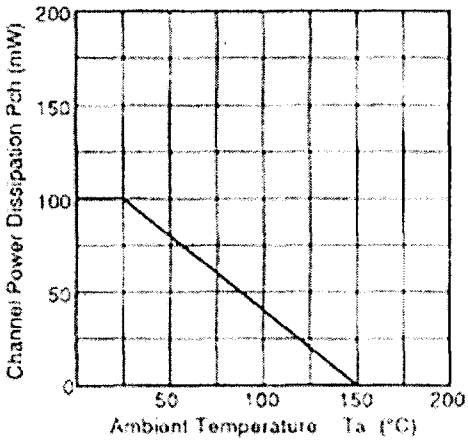
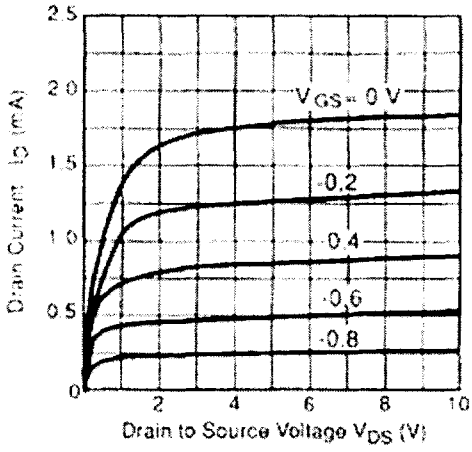
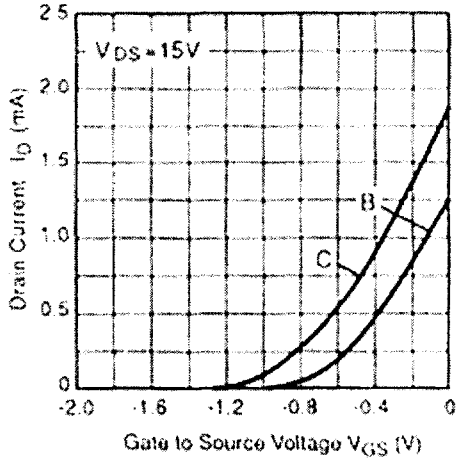
Maximum channel dissipation curve



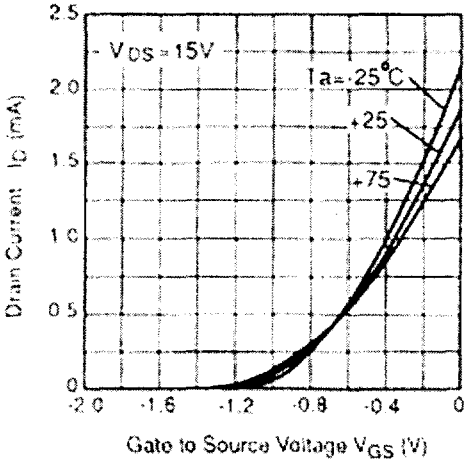
Typical output characteristics



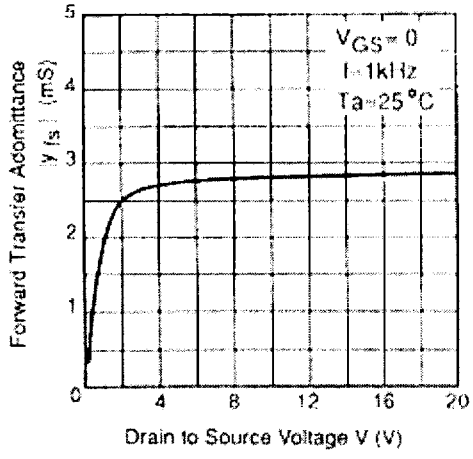
Typical transfer characteristics (1)



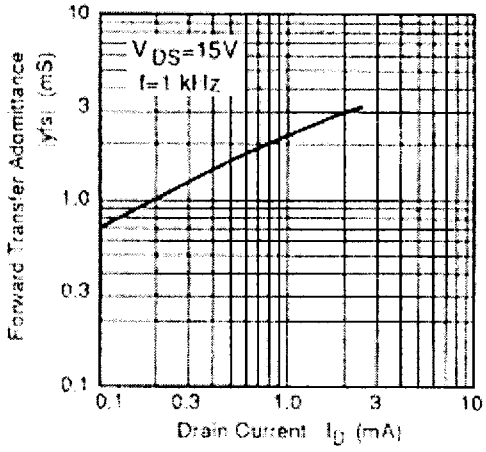
Typical transfer characteristics (2)



Forward transfer admittance
vs. drain to source voltage



Forward transfer admittance
vs. drain current



Capacitance vs. drain to source voltage